**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High voltage capability
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

## 3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions  | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| V <sub>DRM</sub>    | repetitive peak off-<br>state voltage    |   | -   | -   | 800 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5       | -   | -   | 100 | А    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 100 \text{ °C}$ ; Fig. 1;<br>Fig. 2; Fig. 3                         | -   | -   | 12  | А    |
| Static characte     | eristics                                 |   |     |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 7$             | 2   | -   | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$<br>$T_j = 25 \text{ °C; } Fig. 7$ | 2   | -   | 35  | mA   |





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| Symbol | Parameter | Conditions   |  | Min | Тур | Max | Unit |
|--------|-----------|--|--|-----|-----|-----|------|
|        |           | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; |  | 2   | -   | 35  | mA   |
|        |           | T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                  |  |     |     |     |      |

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline                               | Graphic symbol |
|-----|--------|--------------------------------|--|----------------|
| 1   | T1     | main terminal 1                | mb   | T2—T1          |
| 2   | T2     | main terminal 2                | <del>                                     </del> | G<br>sym051    |
| 3   | G      | gate                           |  | ·              |
| mb  | T2     | mounting base; main terminal 2 |  |                |
|     |        |                                | TO-220AB (SOT78)                                 |                |

# 6. Ordering information

Table 3. Ordering information

| Type number    | Package  | ackage   |         |  |  |  |  |
|----------------|----------|--|---------|--|--|--|--|
|                | Name     | Description  | Version |  |  |  |  |
| BTA312-800C    | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |  |
| BTA312-800C/DG | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |  |

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## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max | Unit             |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | 800 | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 100 ^{\circ}\text{C}$ ; Fig. 1;<br>Fig. 2; Fig. 3             | -   | 12  | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 | -   | 100 | А                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 16.7 \text{ ms}$                | -   | 110 | A                |
| I <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t <sub>p</sub> = 10 ms; SIN   | -   | 50  | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$            | -   | 100 | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 2   | Α                |
| P <sub>GM</sub>     | peak gate power                      |   | -   | 5   | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.5 | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40 | 150 | °C               |
| T <sub>j</sub>      | junction temperature                 |   | -   | 125 | °C               |

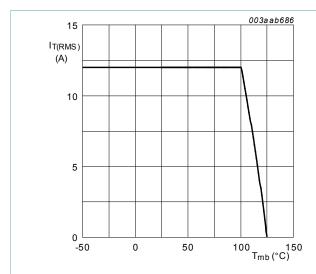
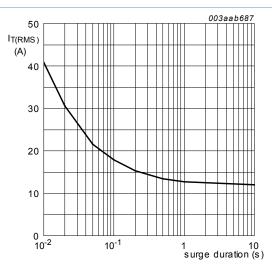


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 100 \text{ }^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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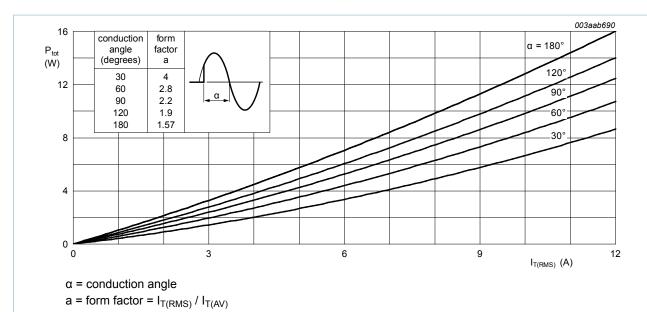


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

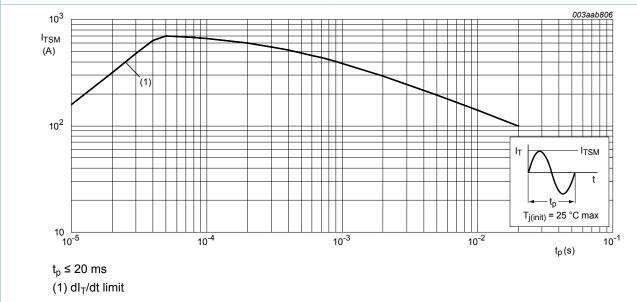


Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

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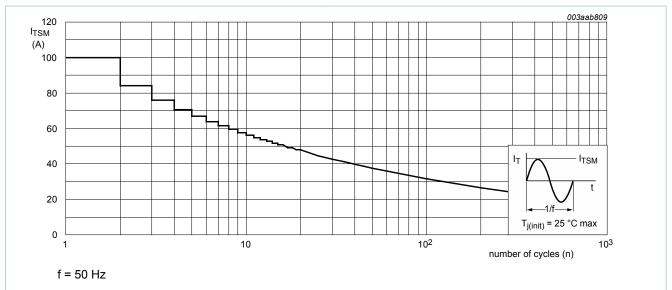


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

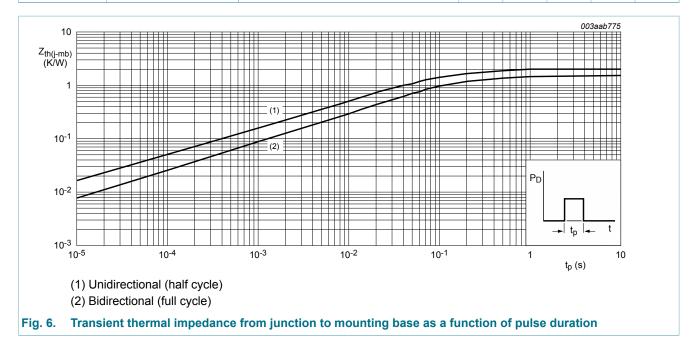
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## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                         | Parameter                                   | Conditions         | Min | Тур | Max | Unit |
|--------------------------------|---|--------------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub>          | thermal resistance                          | full cycle; Fig. 6 | -   | -   | 1.5 | K/W  |
| from junction to mounting base |   | half cycle; Fig. 6 | -   | -   | 2   | K/W  |
| R <sub>th(j-a)</sub>           | thermal resistance from junction to ambient | in free air        | -   | 60  | -   | K/W  |



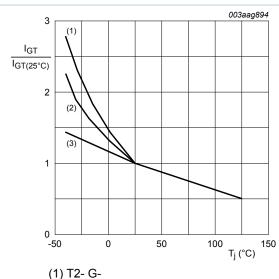
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## 9. Characteristics

Table 6. Characteristics

| Symbol                               | Parameter   | Conditions  | Min  | Тур | Max | Unit |
|--------------------------------------|---|---|------|-----|-----|------|
| Static char                          | acteristics   |   | ,    |     |     |      |
| I <sub>GT</sub> gate trigger current | gate trigger current  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 7$   | 2    | -   | 35  | mA   |
|                                      | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$ | 2   | -    | 35  | mA  |      |
|                                      |   | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$<br>$T_j = 25 \text{ °C; } \underline{Fig. 7}$                     | 2    | -   | 35  | mA   |
| IL                                   | latching current  | $V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 8$  | -    | -   | 50  | mA   |
|                                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 8$     | -   | -    | 60  | mA  |      |
|                                      |   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$                | -    | -   | 50  | mA   |
| I <sub>H</sub>                       | holding current   | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>  | -    | -   | 35  | mA   |
| V <sub>T</sub>                       | on-state voltage  | I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>   | -    | 1.3 | 1.6 | V    |
| V <sub>GT</sub> gate trigger voltage | gate trigger voltage  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11  | -    | 0.8 | 1   | V    |
|                                      |   | V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11   | 0.25 | 0.4 | -   | V    |
| I <sub>D</sub>                       | off-state current   | V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C   | -    | 0.1 | 0.5 | mA   |
| Dynamic cl                           | haracteristics  |   |      |     |     |      |
| dV <sub>D</sub> /dt                  | rate of rise of off-state voltage   | $V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit                    | 500  | -   | -   | V/µs |
| dl <sub>com</sub> /dt                | rate of change of commutating current   | $V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit | 20   | -   | -   | A/ms |

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- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

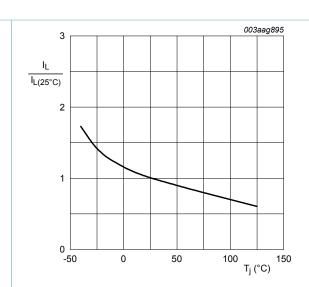


Fig. 8. Normalized latching current as a function of junction temperature

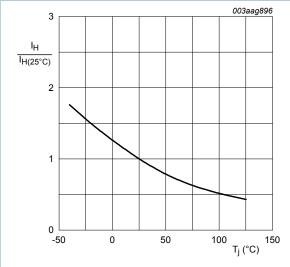
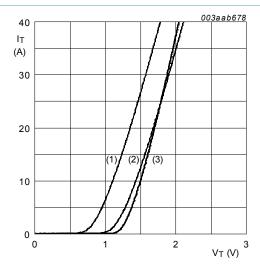


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o$  = 1.164 V;  $R_s$  = 0.027  $\Omega$ 

- (1) T<sub>j</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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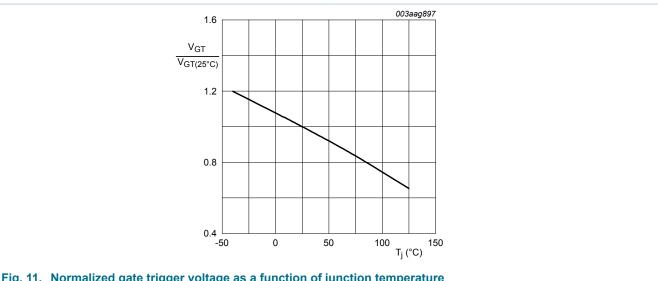
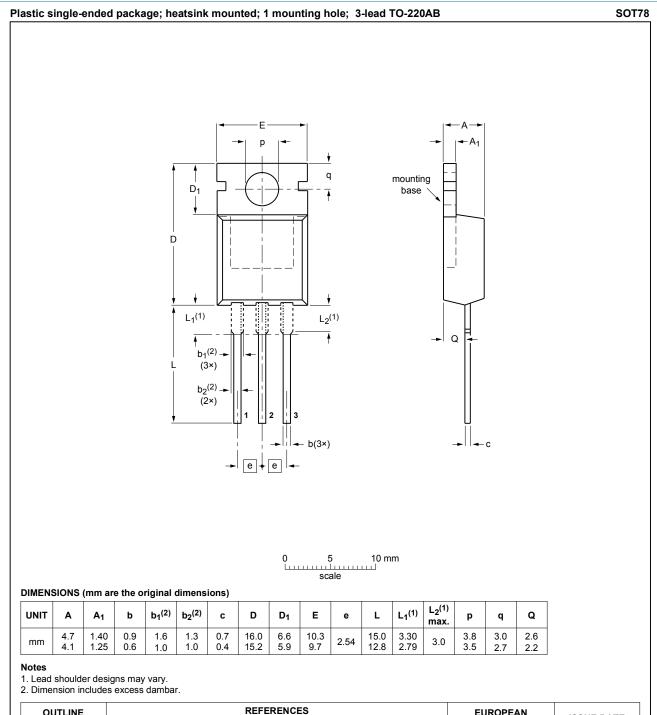


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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# 10. Package outline



| OUTLINE | OUTLINE REFERENCES |                 | EUROPEAN | ISSUE DATE |                                 |
|---------|--------------------|-----------------|----------|------------|---------------------------------|
| VERSION | IEC                | JEDEC           | JEITA    | PROJECTION | ISSUE DATE                      |
| SOT78   |                    | 3-lead TO-220AB | SC-46    |            | <del>08-04-23</del><br>08-06-13 |

Fig. 12. Package outline TO-220AB (SOT78)

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